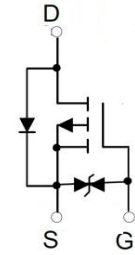




MT3139K P-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20V	510mΩ@-4.5V	-0.75A
	750mΩ@-2.5V	
	960mΩ(TYP)@-1.8V	

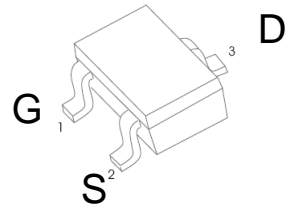


Feature

- Surface Mount Package
- P-Channel Switch with Low RDS(on)
- Operated at Low Logic Level Gate Drive

Application

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics



SOT-23

MARKING: 39K

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±8	V
Continuous Drain Current	I_D	-0.75	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-1.2	A
Power Dissipation ⁽²⁾	P_D	150	mW
Thermal Resistance from Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	833	$^{\circ}C/W$
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$



MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

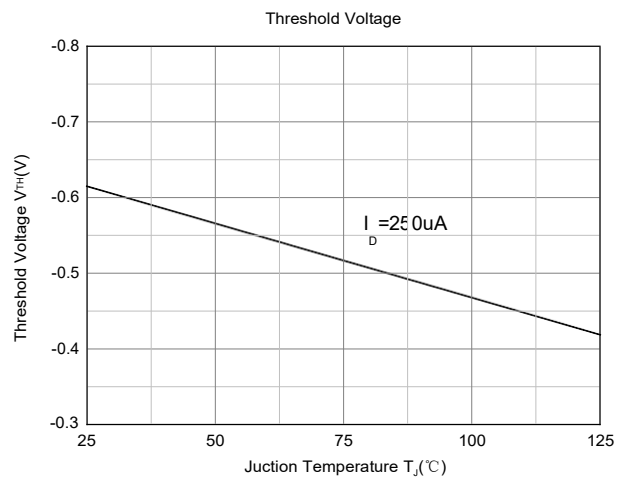
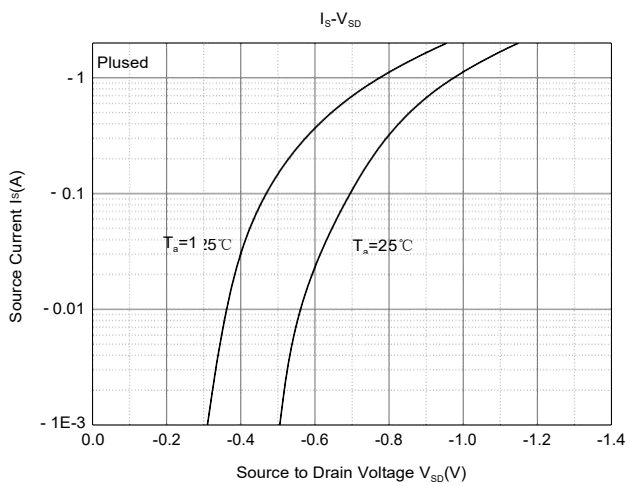
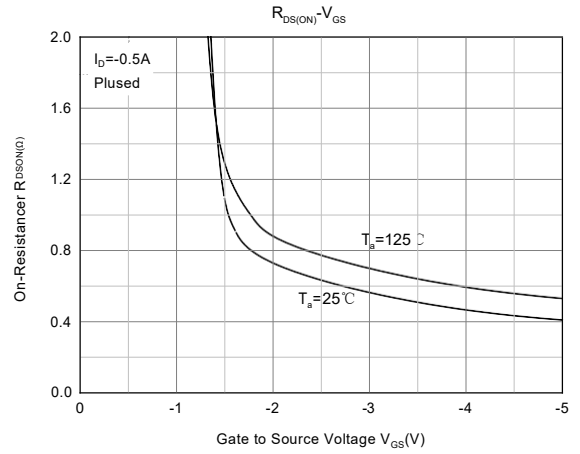
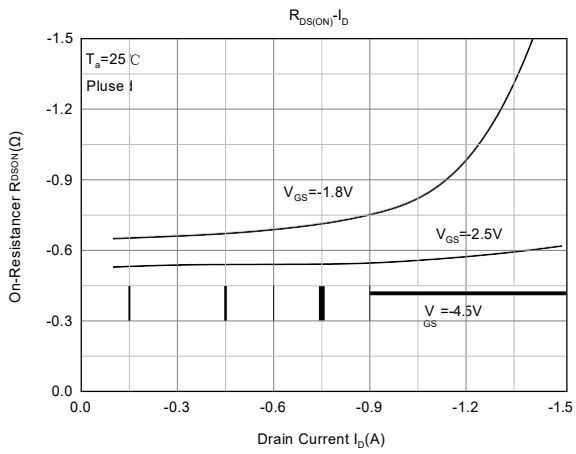
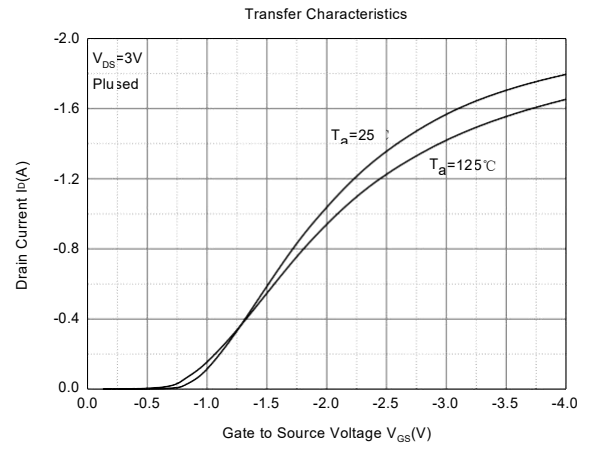
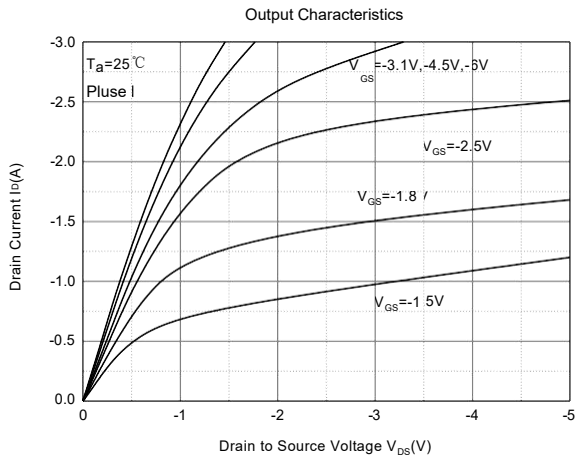
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ± 8 V, V _{DS} = 0V			±20	μA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.35	-0.61	-1.1	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} = -4.5V, I _D = -1A		420	510	mΩ
		V _{GS} = -2.5V, I _D = -0.8A		630	750	
		V _{GS} = -1.8V, I _D = -0.5A		960		
Forward tranconductance	g _{FS}	V _{DS} = -10V, I _D = -0.54A	0.8			S
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C _{iss}	V _{DS} = -16V, V _{GS} = 0V, f = 1MHz		113		pF
Output Capacitance	C _{oss}			15		
Reverse Transfer Capacitance	C _{rss}			9		
Switching Characteristics⁽⁴⁾						
Turn-on delay time	t _{d(on)}	V _{DS} = -10V, I _D = -200mA, V _{GS} = -4.5V, R _G = 10Ω		9		ns
Turn-on rise time	t _r			5.7		
Turn-off delay time	t _{d(off)}			32.6		
Turn-off fall time	t _f			20.3		
Source-Drain Diode characteristics						
Diode forward voltage ⁽³⁾	V _{DS}	I _S = -0.5A, V _{GS} = 0V			-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. This test is performed with no heat sink at T_a=25°C.
3. Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.
4. These parameters have no way to verify.



Typical Electrical and Thermal Characteristics

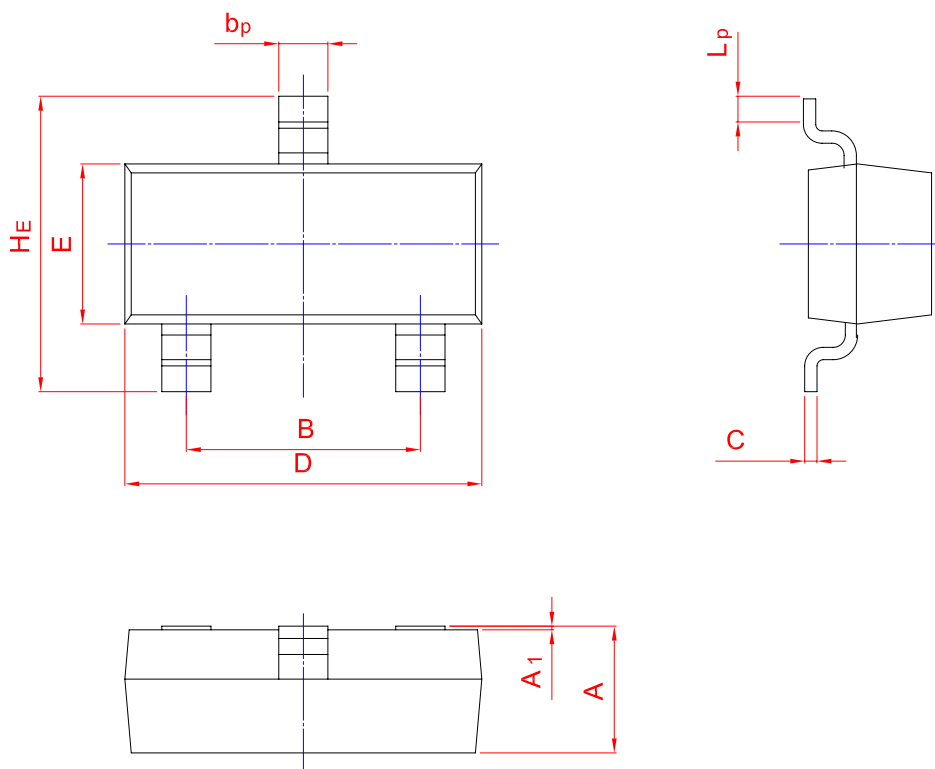
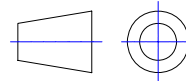




PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20